

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias Plastic -40°C to 85°C
 Storage Temperature -65°C to +160°C
 All Output or Supply Voltages -0.5 to +7 Volts
 All Input Voltages -1.0 to 5.5 Volts
 Output Currents 100mA

**NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

D.C. CHARACTERISTICS (TA = -40°C to 85°C, VCC = +5V ±5%)

Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.	Max.		
IF	Input Load Current, ACK, DS2, CR, DI1-DI8 Inputs			-25	mA	VF = .45V
IF	Input Load Current MD Input			-75	mA	VF = .45V
IF	Input Load Current DS1 Input			-1.0	mA	VF = .45V
IR	Input Leakage Current, ACK, DS, CR, DI1-DI8 Inputs			10	μA	VR ≤ VCC
IR	Input Leakage Current MO Input			30	μA	VR ≤ VCC
IR	Input Leakage Current DS1 Input			40	μA	VR ≤ VCC
Vc	Input Forward Voltage Clamp			-1	V	IC = -5mA
VIL	Input "Low" Voltage			0.85	V	
VIH	Input "High" Voltage	2.0			V	
VOL	Output "Low" Voltage			0.45	V	IOL = 15mA
VOH	Output "High" Voltage	3.65	4.0		V	IOH = -1mA
Isc	Short Circuit Output Current	-15		-75	mA	VO = 0V, VCC = 5V
Io	Output Leakage Current High Impedance State			-20 20	μA μA	VO = .45V VO = 5.25V
Icc	Power Supply Current		90	130	mA	

CAPACITANCE* (F = 1 MHz, VBIAS = 2.5V, VCC = +5V, TA = 25°C)

Symbol	Test	Limits	
		Typ.	Max.
CIN	DS1 MD Input Capacitance	9pF	15 pF
CIN	DS2, CK, ACK, DI1-DI8 Input Capacitance	5pF	10 pF
COUT	DO1-DO8 Output Capacitance	8pF	15 pF

*This parameter is sampled and not 100% tested.

A.C. CHARACTERISTICS ($T_A = -40^\circ\text{C}$ to 85°C , $V_{CC} = +5\text{V} \pm 5\%$)

Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.	Max.		
tpw	Pulse Width	30			ns	
tPD	Data to Output Delay			30	ns	Note 1
tWE	Write Enable to Output Delay			40	ns	Note 1
tSET	Data Set Up Time	15			ns	
tH	Data Hold Time	20			ns	
tR	Reset to Output Delay			40	ns	Note 1
ts	Set to Output Delay			30	ns	Note 1
tE	Output Enable/Disable Time			45	ns	Note 1
tc	Clear to Output Delay			55	ns	Note 1

SWITCHING CHARACTERISTICS**Conditions of Test**

Input Pulse Amplitude = 2.5V

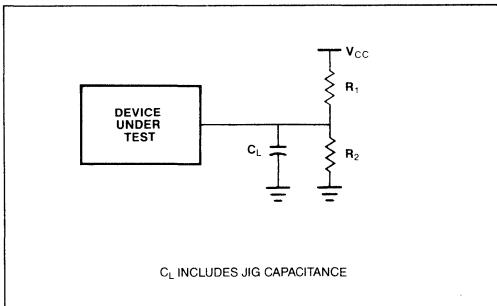
Input Rise and Fall Times 5ns

Between 1V and 2V Measurements made at 1.5V
with 15mA and 30pF Test Load

Note 1:

Test	C_L^*	R_1	R_2
tPD, tWE, tR, ts, tc	30pF	300Ω	600Ω
tE, ENABLE!	30pF	10KΩ	1KΩ
tE, ENABLE !	30pF	300Ω	600Ω
tE, DISABLE!	5pF	300Ω	600Ω
tE, DISABLE!	5pF	10KΩ	1KΩ

*Includes probe and jig capacitance.

A.C. TESTING LOAD CIRCUIT

I8216/I8226 4-BIT PARALLEL BIDIRECTIONAL BUS DRIVER *INDUSTRIAL*

- Data Bus Buffer Driver
- Low Input Load Current — .25 mA Maximum
- High Output Drive Capability for Driving System Data Bus
- 3.65V Output High Voltage
- Three State Outputs
- Reduces System Package Count
- Industrial Temperature Range: —40° to +85°C

The I8216/I8226 is a 4-bit bidirectional bus driver/receiver.

All inputs are low power TTL compatible. For driving MOS, the DO outputs provide a high 3.65V V_{OH} , and for high capacitance terminated bus structures, the DB outputs provide a high 50mA I_{OL} capability.

A non-inverting (I8216) and an inverting (I8226) are available to meet a wide variety of applications for buffering in microcomputer systems.

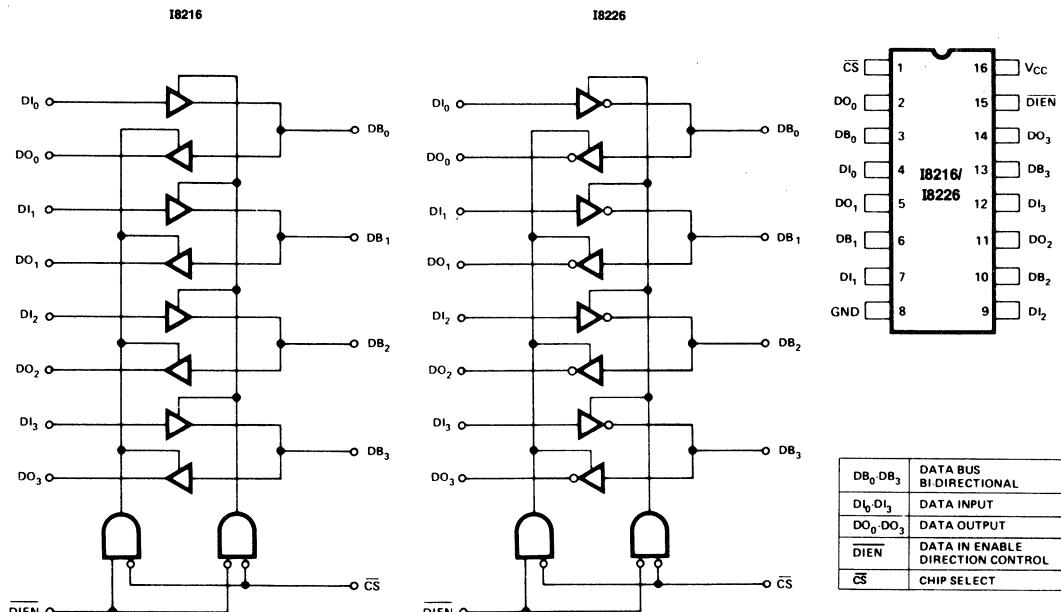


Figure 1. Logic Diagrams

Figure 2. Pin Configuration